

Silicon PNP Power Transistors

2SB656

DESCRIPTION

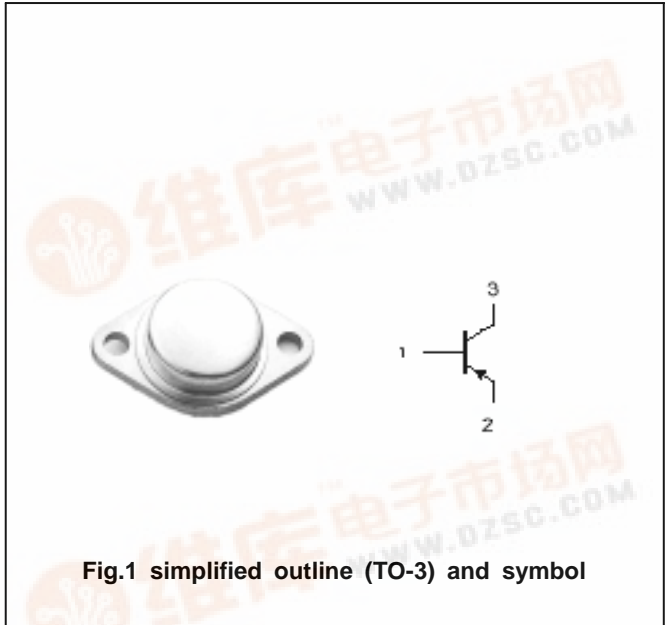
- With TO-3 package
- High power dissipation

APPLICATIONS

- For use in power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta= )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-160	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-160	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-12	A
I <sub>B</sub>	Base current		-4	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25	125	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA ; I <sub>B</sub> =0	-160			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA ; I <sub>E</sub> =0	-160			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-10A ; I <sub>B</sub> =-1A			-3.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-160V ; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	60		200	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-10V		20		MHz

◆ h<sub>FE</sub> Classifications

B	C
60-120	100-200

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PACKAGE OUTLINE

